

**ABSTRACT OF THE DISCLOSURE**

A method for providing contrast for alignment marks after a blanket metal deposition is disclosed. A trench is provided in a first region and a trench is provided in an alignment mark region of a semiconductor wafer. A first metal is deposited on the wafer, and the first metal is blocked from filling the trench in the alignment mark region to maintain the trench in the alignment mark region in an unfilled state. The wafer is planarized to remove the first metal from a top surface. A blanket depositing of a second metal layer is performed on the first region and the alignment mark region such that the trench in the alignment mark region is suitable for use as a scattering alignment mark.